Preferred Devices

# Complementary NPN-PNP Silicon Power Bipolar Transistors

The MJW3281A and MJW1302A are PowerBase  $^{\text{TM}}$  power transistors for high power audio, disk head positioners and other linear applications.

- Designed for 100 W Audio Frequency
- Gain Complementary:

Gain Linearity from 100 mA to 7 A  $h_{FE} = 45$  (Min) @  $I_{C} = 8$  A

- Low Harmonic Distortion
- High Safe Operation Area 1 A/100 V @ 1 Second
- High f<sub>T</sub> 30 MHz Typical

#### **MAXIMUM RATINGS** (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	230	Vdc
Collector–Base Voltage	VCBO	230	Vdc
Emitter-Base Voltage	VEBO	5.0	Vdc
Collector–Emitter Voltage – 1.5 V	VCEX	230	Vdc
Collector Current – Continuous – Peak (Note 1)	IC	15 25	Adc
Base Current – Continuous	ΙΒ	1.5	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate Above 25°C	PD	200 1.43	Watts W/°C
Operating and Storage Junction Temperature Range	TJ, T <sub>stg</sub>	-65 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.7	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	40	°C/W

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle < 10%.



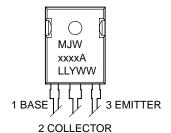
ON Semiconductor™

http://onsemi.com

15 AMPERES
COMPLEMENTARY
SILICON POWER
TRANSISTORS
230 VOLTS
200 WATTS



#### **MARKING DIAGRAM**



MJWxxxxA = Device Code xxxx = 3281 OR 1302 LL = Location Code Y = Year

WW = Work Week

#### ORDERING INFORMATION

Device	Package	age Shipping		
MJW3281A	TO-247	30 Units/Rail		
MJW1302A	TO-247	30 Units/Rail		

**Preferred** devices are recommended choices for future use and best overall value.

## **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	<u>.</u>				
Collector–Emitter Sustaining Voltage (IC = 100 mAdc, I <sub>B</sub> = 0)	VCEO(sus)	230	-	_	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 230 Vdc, I <sub>E</sub> = 0)	ICBO	_	-	50	μAdc
Emitter Cutoff Current (VEB = 5 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	_	-	5	μAdc
SECOND BREAKDOWN					
Second Breakdown Collector with Base Forward Biased (V <sub>CE</sub> = 50 Vdc, t = 1 s (non–repetitive) (V <sub>CE</sub> = 100 Vdc, t = 1 s (non–repetitive)	IS/b	4 1	_ _	_ _	Adc
ON CHARACTERISTICS	1			•	•
DC Current Gain  (IC = 100 mAdc, VCE = 5 Vdc)  (IC = 1 Adc, VCE = 5 Vdc)  (IC = 3 Adc, VCE = 5 Vdc)  (IC = 5 Adc, VCE = 5 Vdc)  (IC = 7 Adc, VCE = 5 Vdc)  (IC = 8 Adc, VCE = 5 Vdc)  (IC = 15 Adc, VCE = 5 Vdc)	h <sub>FE</sub>	50 50 50 50 50 50 45 12	125 - - - 115 - 35	200 200 200 200 200 200 –	-
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 10 Adc, I <sub>B</sub> = 1 Adc)	VCE(sat)	-	0.4	2	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 8 Adc, V <sub>CE</sub> = 5 Vdc)	VBE(on)	_	_	2	Vdc
DYNAMIC CHARACTERISTICS					
Current-Gain - Bandwidth Product (I <sub>C</sub> = 1 Adc, V <sub>CE</sub> = 5 Vdc, f <sub>test</sub> = 1 MHz)	fT	_	30	_	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f <sub>test</sub> = 1 MHz)	C <sub>ob</sub>	_	-	600	pF

#### PNP MJW1302A

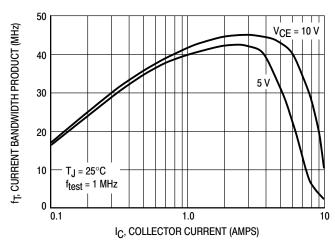


Figure 1. Typical Current Gain Bandwidth Product

#### NPN MJW3281A

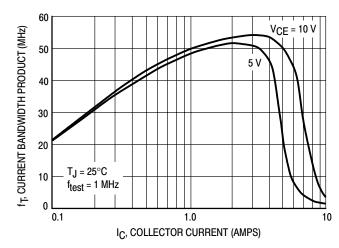


Figure 2. Typical Current Gain Bandwidth Product

#### **TYPICAL CHARACTERISTICS**

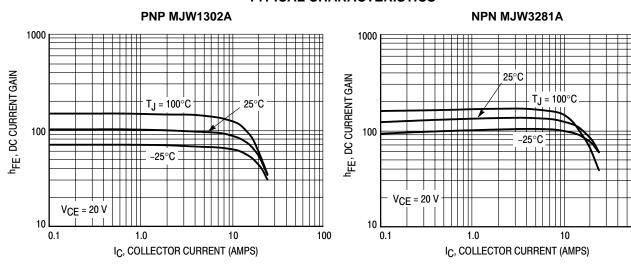


Figure 3. DC Current Gain, VCE = 20 V

Figure 4. DC Current Gain, VCE = 20 V

100

100

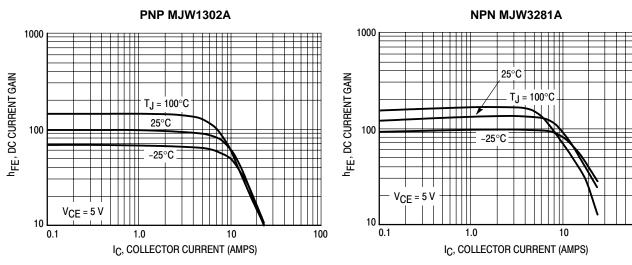


Figure 5. DC Current Gain, VCE = 5 V

Figure 6. DC Current Gain, V<sub>CE</sub> = 5 V

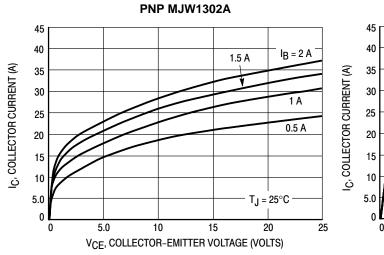


Figure 7. Typical Output Characteristics

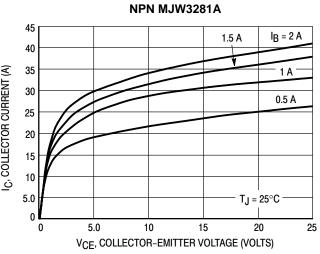


Figure 8. Typical Output Characteristics

#### **TYPICAL CHARACTERISTICS**

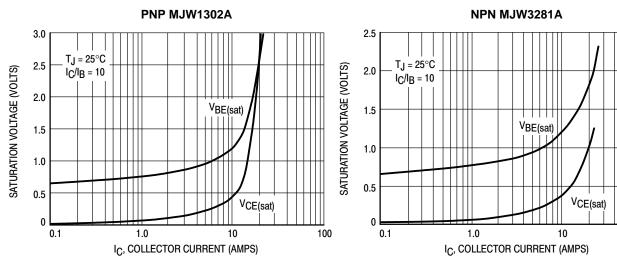


Figure 9. Typical Saturation Voltages

Figure 10. Typical Saturation Voltages

100

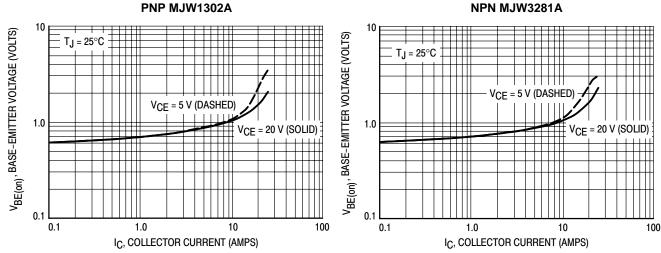


Figure 11. Typical Base-Emitter Voltage

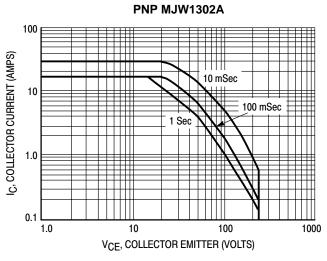


Figure 13. Active Region Safe Operating Area

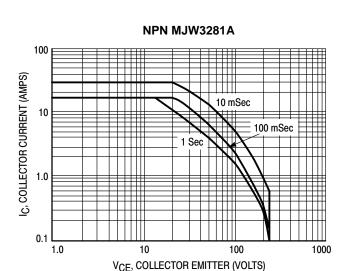


Figure 12. Typical Base-Emitter Voltage

Figure 14. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 13 and 14 is based on  $T_{J(pk)} = 150^{\circ} C$ ;  $T_{C}$  is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

#### TYPICAL CHARACTERISTICS

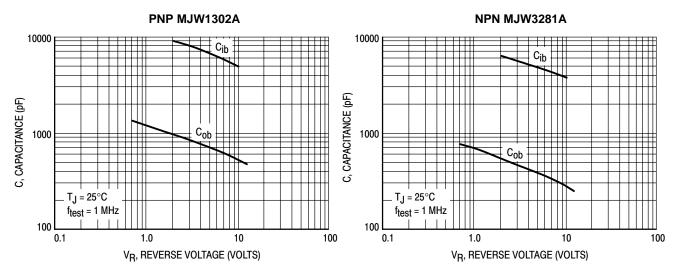
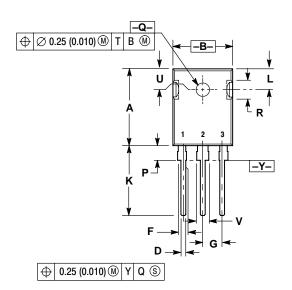


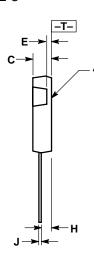
Figure 15. MJW1302A Typical Capacitance

Figure 16. MJW3281A Typical Capacitance

## **PACKAGE DIMENSIONS**

TO-247 CASE 340K-01 ISSUE C





- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	19.7	20.3	0.776	0.799
В	15.3	15.9	0.602	0.626
С	4.7	5.3	0.185	0.209
D	1.0	1.4	0.039	0.055
E	1.27 REF		0.050 REF	
F	2.0	2.4	0.079	0.094
G	5.5 BSC		0.216 BSC	
Н	2.2	2.6	0.087	0.102
J	0.4	0.8	0.016	0.031
K	14.2	14.8	0.559	0.583
L	5.5 NOM		0.217 NOM	
Р	3.7	4.3	0.146	0.169
Q	3.55	3.65	0.140	0.144
R	5.0 NOM		0.197 NOM	
U	5.5 BSC		0.217 BSC	
٧	3.0	3.4	0.118	0.134

STYLE 3: PIN 1. BASE 2. COLLECTOR 3. EMITTER



PowerBase is a trademark of Semiconductor Components Industries, LLC.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

#### PUBLICATION ORDERING INFORMATION

#### Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

**Phone**: 303–675–2175 or 800–344–3860 Toll Free USA/Canada **Fax**: 303–675–2176 or 800–344–3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

**JAPAN**: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–0031

Phone: 81–3–5740–2700 Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local

Sales Representative.